

Amendments to the claims:

This listing of claims will replace all prior versions and listing of claims in the application.

Listing of claims:

1. (Currently amended) A semiconductor device comprising:
an insulation film formed on a substrate;
a buried metal interconnect formed in the insulation film; and
a barrier metal film formed between the insulation film and the metal interconnect,
wherein the barrier metal film is a metal compound film, and
wherein the metal compound film contains at least one of the elements forming the
insulation film and is made of at least one selected from a group consisting of [[Ti,]] Zr, Hf,
[[Nb,]] W, V, Mo, Os, Rh, Ir, Pd and Pt or any alloy thereof.
2. (Withdrawn) The semiconductor device of claim 1, wherein the metal compound film
is a metal nitride film, and
wherein the insulation film contains nitrogen.
3. (Canceled).
4. (Withdrawn) The semiconductor device of claim 1, wherein the metal compound film
is a metal carbide film, and
wherein the insulation film contains carbon.
5. (Withdrawn) The semiconductor device of claim 1, wherein the metal compound film
is a metal silicide film, and
wherein the insulation film contains silicon.
6. (Original) The semiconductor device of claim 1, wherein a metal forming the metal
compound film is a refractory metal.

7. (Original) The semiconductor device of claim 1, wherein the metal interconnect is formed of copper or an copper alloy.

8. (Withdrawn) A semiconductor device comprising:
an insulation film formed on a substrate;
a buried metal interconnect formed in the insulation film; and
a barrier metal film formed between the insulation film and the metal interconnect,
wherein the barrier metal film is formed of a metal compound film provided so as to be in contact with the insulation film and a film including one or more metal-containing layers and formed on the metal compound film, and
wherein the metal compound film contains at least one of elements forming the insulation film.

9. (Withdrawn) The semiconductor device of claim 8, wherein the film including one or more metal-containing layers is formed of a metal film, a metal compound film or a multi-layer film including a combination of selected ones of the metal film and/or the metal compound film.

10. (Withdrawn) The semiconductor device of claim 8, wherein the metal compound film is a metal nitride film, and
wherein the insulation film contains nitrogen.

11. (Withdrawn) The semiconductor device of claim 8, wherein the metal compound film is a metal oxide film, and
wherein the insulation film contains oxygen.

12. (Withdrawn) The semiconductor device of claim 8, wherein the metal compound film is a metal carbide film, and
wherein the insulation film contains carbon.

13. (Withdrawn) The semiconductor device of claim 8, wherein the metal compound

film is a metal silicide film, and
wherein the insulation film contains silicon.

14. (Withdrawn) The semiconductor device of claim 8, wherein a metal forming the metal compound film is a refractory metal.

15. (Withdrawn) The semiconductor device of claim 8, wherein the metal interconnect is formed of copper or a copper alloy.

16. (Withdrawn) A semiconductor device comprising:
an insulation film formed on a substrate;
a buried metal interconnect formed in the insulation film; and
a barrier metal film formed between the insulation film and the metal interconnect,
wherein the barrier metal film is formed of a metal compound film of a metal silicide film
or a metal carbide film provided so as to be in contact with the insulation film, and
wherein the insulation film contains a IV-group element.

17. (Withdrawn) The semiconductor device of claim 16, wherein a metal forming the metal compound film is a refractory metal.

18. (Withdrawn) The semiconductor device of claim 16, wherein the metal interconnect is formed of copper or a copper alloy.

19. (Withdrawn) A semiconductor device comprising:
an insulation film formed on a substrate;
a buried metal interconnect formed in the insulation film; and
a barrier metal film formed between the insulation film and the metal interconnect,
wherein the barrier metal film is formed of a metal compound film of a metal silicide film
or a metal carbide film provided so as to be in contact with the insulation film and a film
including one or more metal-containing layers formed on the metal compound film, and
wherein the insulation film contains a IV-group element.

20. (Withdrawn) The semiconductor device of claim 19, wherein the film including one or more metal-containing layers is formed of a metal film, a metal compound film or a multi-layer film including a combination of selected ones of the metal film and/or the metal compound film.

21. (Withdrawn) The semiconductor device of claim 19, wherein a metal forming the metal compound film is a refractory metal.

22. (Withdrawn) The semiconductor device of claim 19, wherein the metal interconnect is formed of copper or a copper alloy.

23. (Withdrawn) A semiconductor device comprising:
a first insulation film formed on a substrate;
a buried metal interconnect formed in the first insulation film;
a barrier metal film formed between the first insulation film and the metal interconnect,
wherein a second insulation film is formed between the first insulation film and the barrier metal film, and
wherein the barrier metal film is a metal compound film, and
wherein the metal compound film contains at least one of elements forming the second insulation film.

24. (Withdrawn) The semiconductor device of claim 23, wherein a film including one or more metal-containing layers is further formed between the metal compound film and the metal interconnect.

25. (Withdrawn) The semiconductor device of claim 23, wherein the film including one or more metal-containing layers is formed of a metal film, a metal compound film or a multi-layer film including a combination of selected ones of the metal film and/or the metal compound film.

26. (Withdrawn) The semiconductor device of claim 23, wherein the metal compound film is a metal nitride film, and
wherein the second insulation film contains nitrogen.

27. (Withdrawn) The semiconductor device of claim 23, wherein the metal compound film is a metal oxide film, and
wherein the second insulation film contains oxygen.

28. (Withdrawn) The semiconductor device of claim 23, wherein the metal compound film is a metal carbide film, and
wherein the second insulation film contains carbon.

29. (Withdrawn) The semiconductor device of claim 23, wherein the metal compound film is a metal silicide film, and
wherein the second insulation film contains silicon.

30. (Withdrawn) The semiconductor device of claim 23, wherein a metal forming the metal compound film is a refractory metal.

31. (Withdrawn) The semiconductor device of claim 23, wherein the metal interconnect is formed of copper or a copper alloy.

32. (Withdrawn) A semiconductor device comprising:
a first insulation film formed on a substrate;
a buried metal interconnect formed in the first insulation film; and
a barrier metal film formed between the first insulation film and the metal interconnect,
wherein a second insulation film is formed between the first insulation film and the barrier metal film;

wherein the barrier metal film is formed of a metal compound film of a metal silicide film

or a metal carbide film, and

wherein the second insulation film contains a IV-group element.

33. (Withdrawn) The semiconductor device of claim 32, wherein a film including one or more metal-containing layers is further formed between the metal compound film and the metal interconnect.

34. (Withdrawn) The semiconductor device of claim 32, wherein a metal forming the metal compound film is a refractory metal.

35. (Withdrawn) The semiconductor device of claim 32, wherein the metal interconnect is formed of copper or a copper alloy.

36. (Withdrawn) A method for forming a semiconductor device, comprising the steps of:

forming a recess portion in an insulation film formed on a substrate;

forming a barrier metal film of a metal compound film containing at least one of elements forming the insulation film so that the barrier metal film covers at least surfaces of the recess portion; and

forming a buried metal interconnect on the barrier metal film so that the buried metal interconnect fills the recess portion.

37. (Withdrawn) The method of claim 36, further comprising the steps of:

forming a recess portion in a first insulation film formed on a substrate;

forming a second insulation film so that the second insulation film covers at least surfaces of the recess portion;

forming, on the second insulation film, a metal compound film containing at least one of elements forming the second insulation film; and

forming a buried metal interconnect on the metal compound film so that the buried metal interconnect fills the recess portion.

38. (Withdrawn) The method of claim 36, wherein the step of forming a barrier metal film includes the step of further forming, after formation of the metal compound film, a film including one or more metal-containing layers on the metal compound film to obtain the barrier metal film including the metal compound film and the film including one or more layer of one or more metals.

39. (Withdrawn) The method of claim 38, wherein the film including one or more metal-containing layers is a metal film, a metal compound film or a multi-layer film including a combination of selected ones of the metal film and/or the metal compound film.

40. (Withdrawn) The method of claim 36, wherein the metal oxide film is a metal nitride film, and
wherein the insulation film formed so as to be adjacent to the metal compound film contains nitrogen.

41. (Withdrawn) The method of claim 36, wherein the metal compound film is a metal oxide film, and
wherein the insulation film formed so as to be adjacent to the metal compound film contains oxygen.

42. (Withdrawn) The method of claim 36, wherein the metal compound film is a metal carbide film, and
wherein the insulation film formed so as to be adjacent to the metal compound film contains carbon.

43. (Withdrawn) The method of claim 36, wherein the metal compound film is a metal silicide film, and
wherein the insulation film formed so as to be adjacent to the metal compound film contains silicon.

44. (Withdrawn) The method of claim 36, wherein a metal forming the metal compound

film is a refractory metal.

45. (Withdrawn) The method of claim 36, wherein the metal interconnect is formed of copper or a copper alloy.

46. (Withdrawn) A method for fabricating a semiconductor device, comprising the steps of:

forming a recess portion in an insulation film formed on a substrate and containing a IV-group element;

forming a barrier metal film including a metal compound film of a metal silicide film or a metal carbide film so that the barrier metal film covers at least surfaces of the recess portion; and

forming a buried metal interconnect on the barrier metal film so that the buried metal interconnect fills the recess portion.

47. (Withdrawn) The method of claim 46, wherein the step of forming a barrier metal film includes the step of forming, after formation of the metal compound film, a film including one or more metal-containing layers on the metal compound film to obtain the barrier metal film including the metal compound film and the film including one or more metal-containing layers.

48. (Withdrawn) The method of claim 46, wherein a metal forming the metal compound film is a refractory metal.

49. (Withdrawn) The method of claim 46, wherein the metal interconnect is formed of copper or a copper alloy.

50. (Withdrawn) A method for fabricating a semiconductor device, comprising the steps of:

forming a recess portion in a first insulation film formed on a substrate;

forming a second insulation film including a IV-group element so that the second insulation film covers at least surfaces of the recess portion;

forming, on the second insulation film, a barrier metal film including a metal compound

film of a metal silicide film or a metal carbide film; and

forming a buried metal interconnect on the barrier metal film so that the metal interconnect fills the recess portion.

51. (Withdrawn) The method of claim 50, wherein the step of forming the barrier metal film includes the step of forming, after formation of the metal compound film, a film including one or more metal-containing layers on the metal compound film to obtain the barrier metal film including the metal compound film and the film including one or more metal-containing layers.

52-53. (Cancelled).

54. (Previously Presented) The semiconductor device of claim 1, wherein the insulation film is SiO_2 , SiOF_2 , SiOC , SiON , SiOCN , or an organic film containing oxygen.

55. (Previously Presented) The semiconductor device of claim 1, wherein the insulation film is nitride carbide or silicide.